



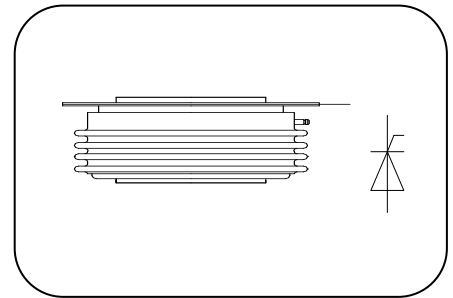
Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$ 3000A
 V_{DRM}/V_{RRM} 2400~2500V
 t_q 40~80 μ s
 I_{TSM} 44 kA
 I^2t 9680 10³A²S



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, T _C =55°C	125		3000	3800	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V_{DRM} & V_{RRM} , tp=10ms V_{DSM} & $V_{RSM}=V_{DRM}$ & $V_{RRM}+100V$	125	1900		2500	V
I_{DRM} I_{RRM}	Repetitive peak current	$V_D=V_{DRM}$ $V_R=V_{RRM}$	125			250	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			62	kA
I^2t	I ² T for fusing coordination	$V_R=0.6V_{RRM}$	125			19220	A ² s*10 ³
V_{TO}	Threshold voltage		125			1.32	V
r_T	On-state slop resistance					0.14	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=5000A$, F=70kN	25			3.00	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/ μ s
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$, ITM to4000A, t=5s Gate pulse t _r ≤0.5 μ s I _{GM} =1.5A f=50Hz	125			600	A/ μ s
Q _{rr}	Recovery charge	$I_{TM}=2000A$, tp=1000 μ s, di/dt=-20A/ μ s, V _R =100V	125		2100		μ C
t _q	Circuit commutated turn-off time	$I_{TM}=2000A$, tp=1000 μ s, V _R =100V dv/dt=30V/ μ s , di/dt=-20A/ μ s	125	40		80	μ s
I_{GT}	Gate trigger current			40		250	mA
V_{GT}	Gate trigger voltage	$V_A=12V$, I _A =1A	25	0.9		2.5	V
I_H	Holding current			20		400	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine' double side cooled Clamping force 70 kN				0.007	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.002	
F _m	Mounting force			63		84	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				1460/1880		g
Outline	KT95cT/dT						

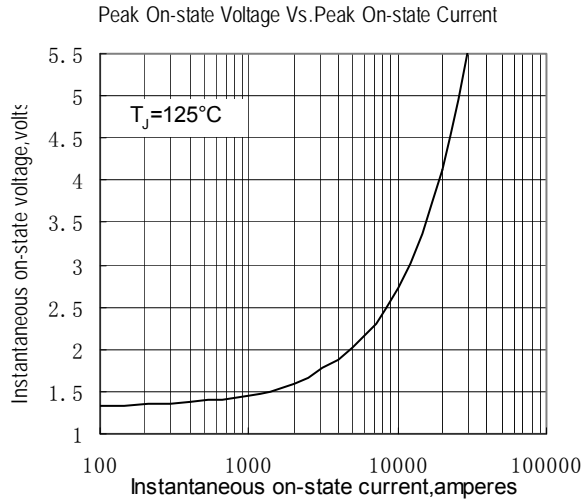


Fig.1

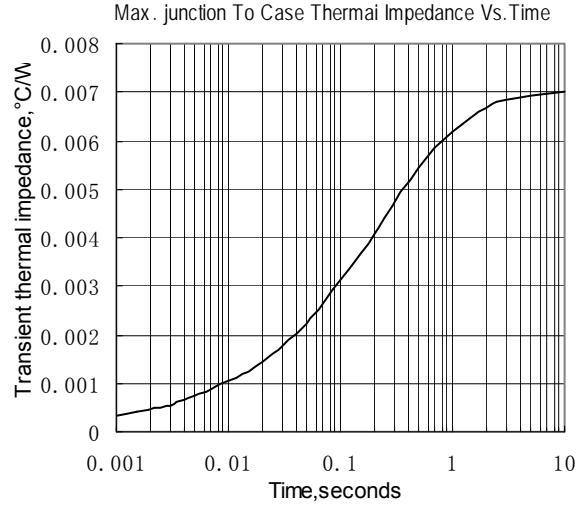


Fig.2

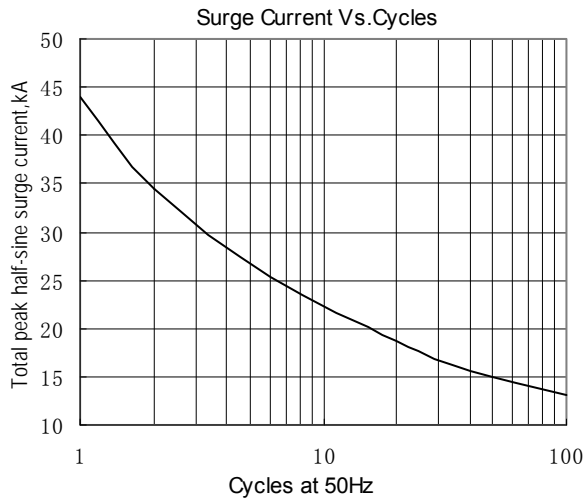


Fig.3

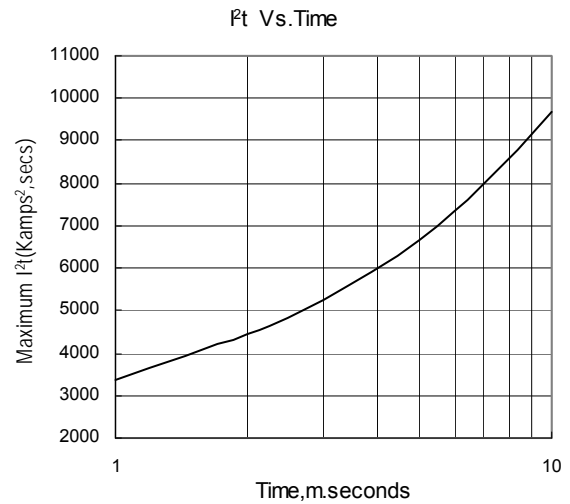


Fig.4

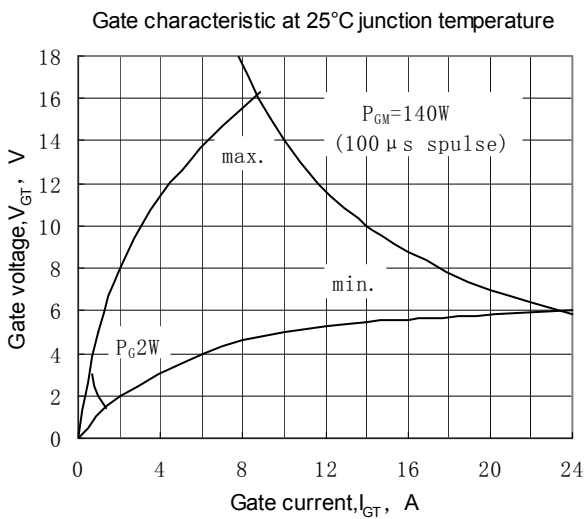


Fig.5

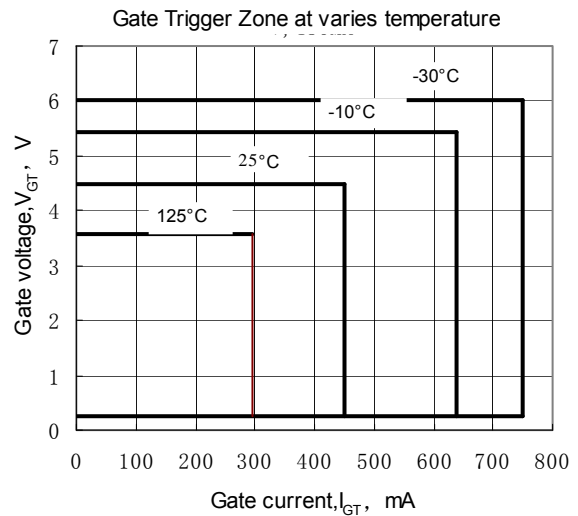


Fig.6



Outline:

图19-KT95cT

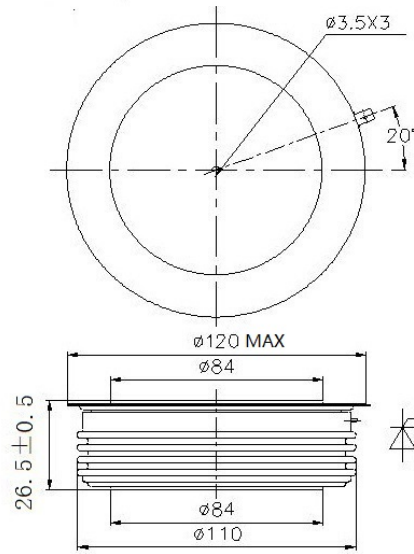
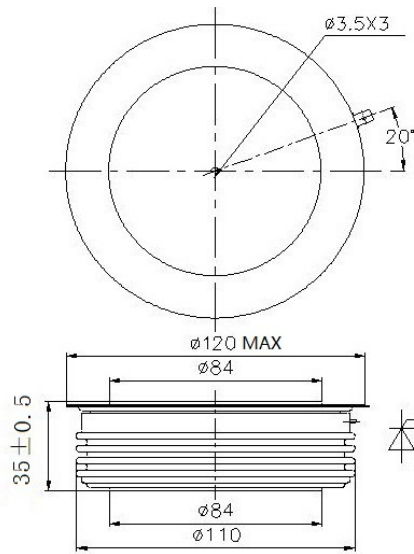


图20-KT95dT



地 址 Address: 辽宁省锦州市滨海新区黔江街21号

邮 编 Zipcode: 121007

电 话 Telephone: 0416-2936666 18840127688

传 真 Fax: 0416-2936888

网 址 Web Sit: <http://www.power-semi.com>

电子邮箱 Email: 13904168481@126.com